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INFORMATION DISCLOSURE CITATION PAGE 1 OF 1				Atty Docket No. OPE-002		Serial No. 09/556,285	
				Applicant G. Taylor			
				Filed April 24, 2000		Group 2811	
US PATENT DOCUMENTS							
Examiner Initials		Document No.	Date	Name	Class	Sub- class	Filing date if approp.
QKH	A	4,229,752	10/21/80	Hynecek	357	24	
	B	4,584,697	04/22/86	Hazendonk et al.	377	60	
	C	4,949,350	08/14/90	Jewell et al.	372	45	
	D	4,995,061	02/19/91	Hynecek	377	58	
QKH	E	5,517,244	05/14/96	Stekelenburg et al.	348	305	
	F						
	G						
	H						
	I						
	J						
	K						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
QKH	1	P.A. Kiley et al., <u>Submicrometre Gate Length Scaling of Inversion Channel Heterojunction Field Effect Transistor</u> , Electronic Letters 3/17/94, Vol 30, No. 6 pp. 529 - 531					
QKH	2	G.W. Taylor and P.A. Kiely, <u>Theoretical and Experimental Results for the Inversion Channel Heterostructure Field Effect Transistor</u> , IEE PROCEEDINGS-G, Vol. 140, No. 6, December 1993:					
QKH	3	S.V. Bandara et al., <u>Broad-band GaAs/AlxGa1-xAs QWIPS</u> , NASA Tech Brief Vol. 23, No. 4 (from JPL New Technology Report NPO-20319), April 1999					
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EXAMINER G. MUNSON				DATE CONSIDERED 15 APRIL 2003			

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